TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT50N322A

Voltage Resonance Inverter Switching Application Fifth Generation IGBT

· FRD included between emitter and collector

• Enhancement mode type

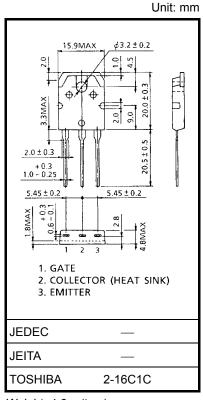
• High speed IGBT : $t_f = 0.10 \mu s$ (typ.) ($I_C = 60 A$)

FRD : $t_{rr} = 0.8 \,\mu s$ (typ.) (di/dt = -20 A/ μs)

Low saturation voltage: V_{CE} (sat) = 2.2 V (typ.) (I_C = 60 A)

Absolute Maximum Ratings (Ta = 25°C)

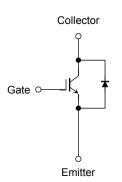
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1000	V	
Gate-emitter voltage		V _{GES}	± 25	V	
Collector current	DC	IC	50	А	
	1ms	I _{CP}	120		
Diode forward current	DC	lF	15	Α	
	1ms	I _{FP}	120		
Collector power dissipation ($Tc = 25^{\circ}C$)		P _C	156	W	
Junction temperature		Tj	150	°C	
Storage temperature		T _{stg}	-55 to 150	°C	



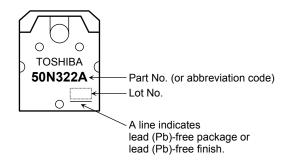
Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit



Marking

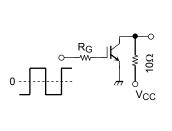


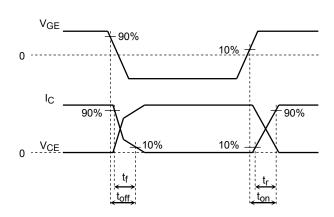
Electrical Characteristics (Ta = 25°C)

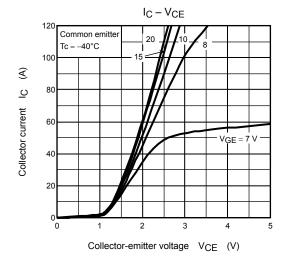
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	± 500	nA
Collector cut-off current		I _{CES}	V _{CE} = 1000 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE} (OFF)	$I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	_	6.0	V
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 60 A, V _{GE} = 15 V	_	2.2	2.8	V
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	4000	_	pF
Switching time	Rise time	t _r	Resistive Load	_	0.23	_	μs
	Turn-on time	t _{on}	V _{CC} = 600 V, I _C = 60 A	_	0.33	_	
	Fall time	t _f	$V_{GG} = \pm 15 \text{ V}, R_G = 51 \Omega$	_	0.10	0.25	
	Turn-off time	t _{off}	(Note 1)	_	0.70	_	
Diode forward voltage		V _F	I _F = 15 A, V _{GE} = 0	_	1.2	1.9	V
Reverse recovery time		t _{rr}	$I_F = 15 \text{ A}, V_{GE} = 0, di/dt = -20 \text{ A/}\mu\text{s}$	_	0.8	_	μs
Thermal Resistance R		Rth(j-c)	_	_	_	0.8	°C/W
Thermal Resistance		Rth(j-c)	_	_	_	4.0	°C/W

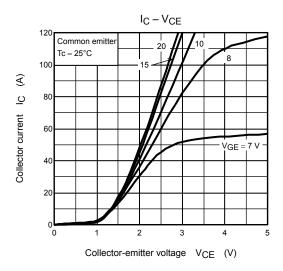
2

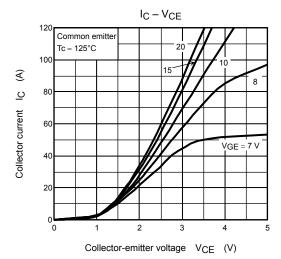
Note 1: Switching time measurement circuit and input/output waveforms

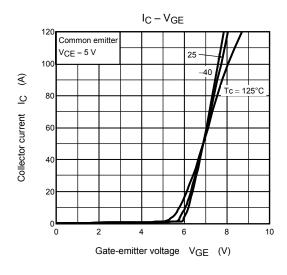


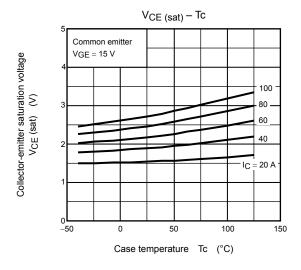


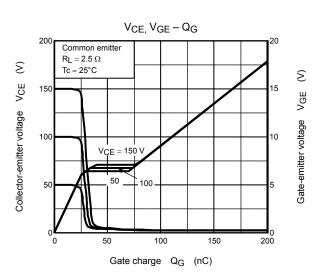


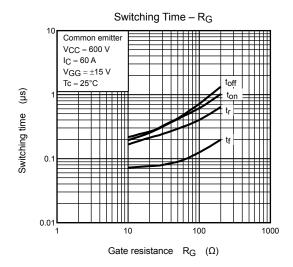


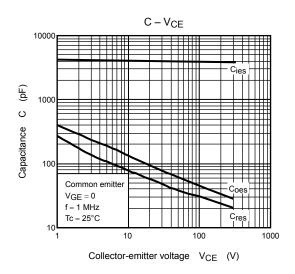


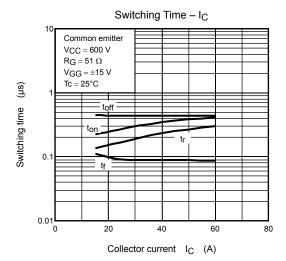


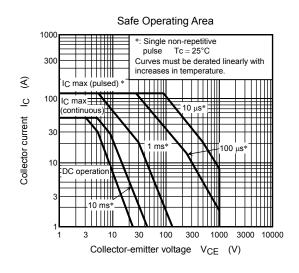


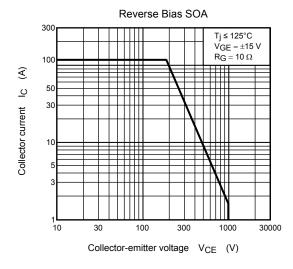


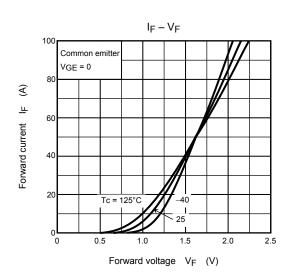


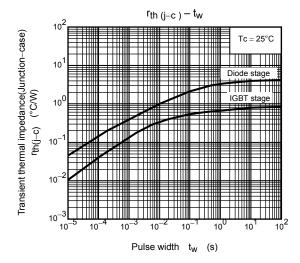


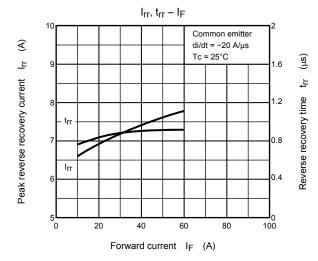


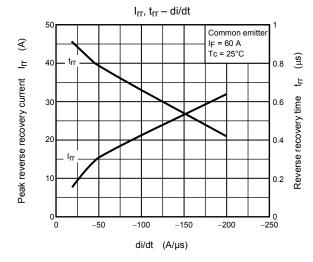












5 2008-01-11

RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for IGBT Transistors category:

Click to view products by Toshiba manufacturer:

Other Similar products are found below:

 748152A
 APT20GT60BRDQ1G
 APT50GT60BRG
 NGTB10N60FG
 STGFW20V60DF
 APT30GP60BG
 APT45GR65B2DU30

 GT50JR22(STA1ES)
 TIG058E8-TL-H
 VS-CPV364M4KPBF
 NGTB25N120FL2WAG
 NGTG40N120FL2WG
 RJH60F3DPQ-A0#T0

 APT40GR120B2SCD10
 APT15GT120BRG
 APT20GT60BRG
 NGTB75N65FL2WAG
 NGTG15N120FL2WG
 IXA30RG1200DHGLB

 IXA40RG1200DHGLB
 APT70GR65B2DU40
 NTE3320
 IHFW40N65R5SXKSA1
 APT70GR120J
 APT35GP120JDQ2

 IKZA40N65RH5XKSA1
 IKFW75N65ES5XKSA1
 IKFW50N65ES5XKSA1
 IKFW50N65EH5XKSA1
 IKFW40N65ES5XKSA1

 IKFW60N65ES5XKSA1
 IMBG120R090M1HXTMA1
 IMBG120R220M1HXTMA1
 XD15H120CX1
 XD25H120CX0
 XP15PJS120CL1B1

 IGW30N60H3FKSA1
 STGWA8M120DF3
 IGW08T120FKSA1
 IGW75N60H3FKSA1
 HGTG40N60B3
 FGH60N60SMD_F085

 FGH75T65UPD
 STGWA15H120F2
 IKA10N60TXKSA1
 IHW20N120R5XKSA1
 RJH60D2DPP-M0#T2
 IKP20N60TXKSA1

 IHW20N65R5XKSA1
 IDW40E65D2FKSA1